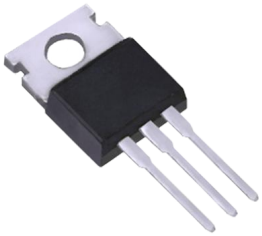
6.0A, 800V N-CHANNEL POWER MOSFET



TO-220

TO-220F

■ DESCRIPTION

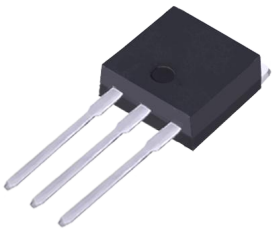
The UTC **6N80** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **6N80** is universally applied in high efficiency switch mode power supply.

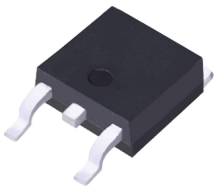
■ FEATURES

* $R_{DS(on)}$ = 2.0Ω @V_{GS} = 10 V
* Improved dv/dt capability
* Fast switching
* 100% avalanche tested

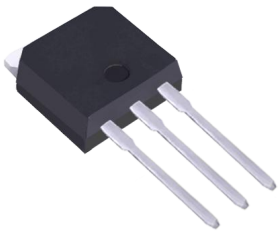
■ SYMBOL



TO-262



TO-263



TO-251

TO-252

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current (Note 2)	Continuous	I_D	6	A
	Pulsed	I_{DM}	22	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	680	mJ
	Repetitive (Note 2)	E_{AR}	15.8	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	138	W
	TO-220F/TO220F1		51	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L = 37mH, I_{AS} = 6A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 5.5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220/TO-262	θ_{JC}	0.9	°C/W
	TO-220F/TO220F1		2.45	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	800			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	Reference to 25°C, I_D=250μA		0.97		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=800V, V_{GS}=0V			10	μA
			V_{DS}=640V, T_C=125°C			100	
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=3A		1.6	2.0	Ω
Forward Transconductance		g_{FS}	V_{DS}=50V, I_D=3A (Note 1)		5.4		S
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1010	1310	pF
Output Capacitance		C_{OSS}			90	115	pF
Reverse Transfer Capacitance		C_{RSS}			8	11	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=640V, I_D=6A (Note 1, 2)		21	30	nC
Gate to Source Charge		Q_{GS}			6		nC
Gate to Drain Charge		Q_{GD}			9		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=400V, I_D=6A, R_G=25Ω (Note 1, 2)		26	60	ns
Rise Time		t_R			65	140	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			47	105	ns
Fall-Time		t_F			44	90	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				6	A
Maximum Body-Diode Pulsed Current		I_{SM}				22	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=6A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_S=6A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		615		ns
Reverse Recovery Charge		Q_{RR}			5.4		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.